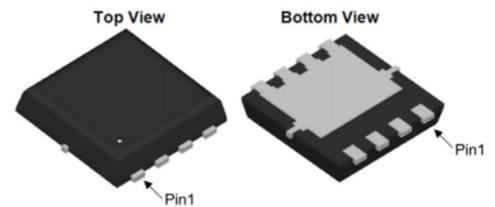


30V N-channel Enhancement MOSFET

Features

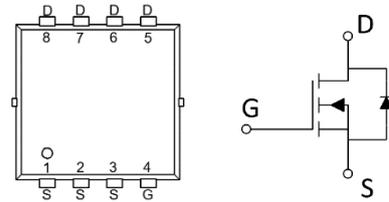
- $V_{DS}=30V, I_D=60A$
- $R_{DS(ON)}=4.2m\Omega$ (TYP.) $V_{GS}=10V, I_D=20A$
- $R_{DS(ON)}=6.2m\Omega$ (TYP.) $V_{GS}=4.5V, I_D=20A$
- Reliable and Rugged
- Avalanche Rated
- Low On-Resistance
- High Current Capability
- Halogen and Antimony Free, RoHS compliant

PDFN5060



Applications

- Load Switch
- Power management in portable/desktop PCs
- DC/DC conversion



Ordering Information

Orderable Device	Package	Package Qty.
CX3060	DFN5X6	5000pcs/Reel

Absolute Maximum Ratings ($T_C=25^\circ C$, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	30	V
Gate-Source Voltage ($V_{GS}=0V$, static)	V_{GS}	± 20	V
Continuous Drain Current ($T_C=25^\circ C$)	I_D	60	A
Continuous Drain Current ($T_C=100^\circ C$)		42	A
Pulsed Drain Current	I_{DM}	240	A
Avalanche Current ($L=0.1mH$)	I_{AS}	35	A
Single Pulsed Avalanche Energy	E_{AS}	61	mJ
Maximum Power Dissipation ($T_C = 25^\circ C$)	P_D	35.7	W
Maximum Power Dissipation ($T_C = 100^\circ C$)		14	W
Operating, Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ C$